TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type (U-MOSVI-H)

# **TPCA8052-H**

Switching Regulator Applications Motor Drive Applications DC-DC Converter Applications

- Small footprint due to a small and thin package
- · High-speed switching
- Small gate charge: Q<sub>SW</sub> = 6.8 nC (typ.)
- Low drain-source ON-resistance:  $R_{DS (ON)} = 7.2 \text{ m}\Omega$  (typ.)
- High forward transfer admittance: |Yfs| = 58 S (typ.)
- Low leakage current:  $I_{DSS} = 10 \mu A \text{ (max) (V}_{DS} = 40 \text{ V)}$
- Enhancement mode:  $V_{th}$  = 1.3 to 2.3 V ( $V_{DS}$  = 10 V,  $I_D$  = 0.2 mA)

### Absolute Maximum Ratings (Ta = 25°C)

Characte	eristic	Symbol	Rating	Unit	
Drain-source voltage		$V_{DSS}$	40	V	
Drain-gate voltage (R	GS = 20 kΩ)	$V_{DGR}$	40	V	
Gate-source voltage		V <sub>GSS</sub>	±20	V	
Drain current	DC (Note 1)	ID	20	Α	
Drain current	Pulsed (Note 1)	$I_{DP}$	60 30	, ,	
Drain power dissipati	on (Tc = 25°C)	P <sub>D</sub>	30	W	
Drain power dissipati	on (t = 10 s) (Note 2a)	$P_{D}$	2.8	W	
Drain power dissipati	on (t = 10 s) (Note 2b)	P <sub>D</sub>	1.6	W	
Single-pulse avalance	ne energy (Note 3)	E <sub>AS</sub>	37	mJ	
Avalanche current		I <sub>AR</sub>	20	Α	
Repetitive avalanche (To	energy c = 25°C) (Note 4)	E <sub>AR</sub>	2.24	mJ	
Channel temperature		T <sub>ch</sub>	150	°C	
Storage temperature	range	T <sub>stg</sub>	-55 to 150	°C	

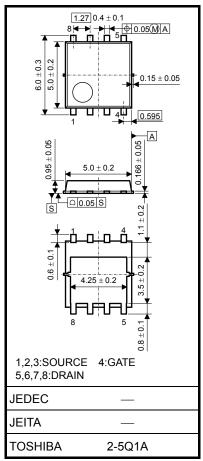
Note: For Notes 1 to 4, refer to the next page.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e.

operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

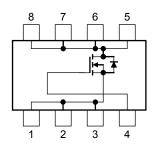
This transistor is an electrostatic-sensitive device. Handle with care.

Unit: mm



Weight: 0.069 g (typ.)

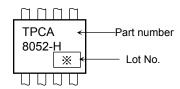
### **Circuit Configuration**



#### **Thermal Characteristics**

Characteristic	Symbol	Max	Unit
Thermal resistance, channel to case (Tc = 25°C)	R <sub>th (ch-c)</sub>	4.17	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2a)	R <sub>th (ch-a)</sub>	44.6	°C/W
Thermal resistance, channel to ambient $(t = 10 \text{ s})$ (Note 2b)	R <sub>th (ch-a)</sub>	78.1	°C/W

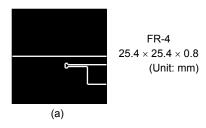
## Marking (Note 5)

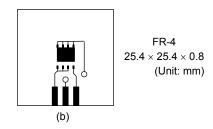


Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: (a) Device mounted on a glass-epoxy board (a)

(b) Device mounted on a glass-epoxy board (b)

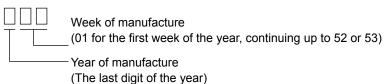




Note 3: V<sub>DD</sub> = 24 V, T<sub>ch</sub> = 25 °C (initial), L = 100  $\mu$ H, R<sub>G</sub> = 25  $\Omega$ , I<sub>AR</sub> = 20 A

Note 4: Repetitive rating: pulse width limited by maximum channel temperature

Note 5: \* Weekly code: (Three digits)





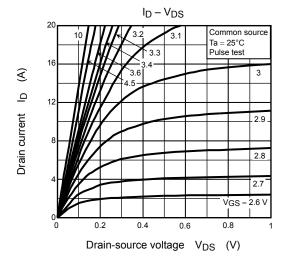
# **Electrical Characteristics (Ta = 25°C)**

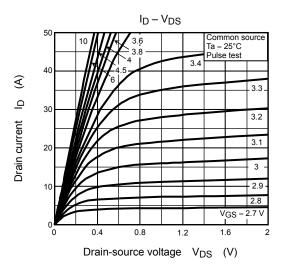
Ch	aracteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cur	rent	I <sub>GSS</sub>	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±100	nA
Drain cutoff curre	ent	I <sub>DSS</sub>	V <sub>DS</sub> = 40 V, V <sub>GS</sub> = 0 V		_	10	μА
Drain agurag bro	akdawa yaltaga	V (BR) DSS	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	40	- + 100 10 - 10 10 23 2.3 - 9.1 13.1 - 7.2 11.3 - 9.58 1620 2110 - 85 130 - 280 - 2.3 - 2.4 8.4 8.0 - 35 - 25 25	V	
Drain-source brea	akuowii voitage	V (BR) DSX	$I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$	23	_	_	v
Gate threshold vo	oltage	V <sub>th</sub>	$V_{DS} = 10 \text{ V}, I_D = 0.2 \text{ mA}$	1.3	_	2.3	٧
Drain cource ON	rosistanco	Pro (ov)	$V_{GS} = 4.5 \text{ V}, I_D = 10 \text{ A}$	_	9.1	13.1	m0
Drain-source ON-resistance		KDS (ON)	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 10 A	_	7.2	11.3	mΩ
Forward transfer	admittance	Y <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 10 A	29	58	_	S
Input capacitance	9	C <sub>iss</sub>		_	1620	2110	
Reverse transfer capacitance		C <sub>rss</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	85	130	pF
Reverse transfer capacitance  Output capacitance  Gate resistance		Coss			280	_	
Gate resistance		rg	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 5 \text{ MHz}$	_	2.3	3.5	Ω
	Rise time	t <sub>r</sub>	10 V □ Ip = 10 A	_	2.4	_	
Conitabilia a tima a	IDSS   VDS = 40 V, VGS = 0 V	_					
Switching time	Fall time	t <sub>f</sub>	R <sub>L</sub> = 2.0	_	8.0	2.3 1 13.1 2 11.3 8 — 20 2110 5 130 0 — 3 3.5 4 — 4 — 0 — 5 — 5 — 6 — 8 —	ns
	Turn-off time	t <sub>off</sub>		_	35	_	
Total gate charge	· •	$V_{DD} \approx 32 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$ — 25 —		_			
(gate-source plus		ųg	$V_{DD} \approx 32 \text{ V}, V_{GS} = 5 \text{ V}, I_D = 20 \text{ A}$	_	13	_	
Gate-source charge 1		Q <sub>gs1</sub>		_	5.6	_	nC
Gate-drain ("Miller") charge		Q <sub>gd</sub>	$V_{DD} \approx 32 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$	_	3.8	_	
Gate switch char	ge	Q <sub>SW</sub>	]	_	6.8	_	

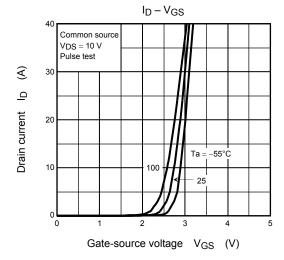
# **Source-Drain Ratings and Characteristics (Ta = 25°C)**

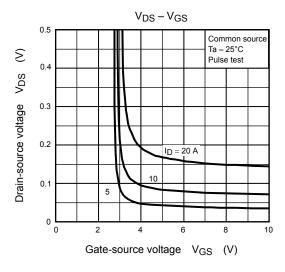
Characteristic		Symbol	Test Condition	Min	Тур.	Max	Unit	
Drain reverse current	Pulse	(Note 1)	I <sub>DRP</sub>	_	_	_	60	Α
Forward voltage (diode)			$V_{DSF}$	$I_{DR} = 20 \text{ A}, V_{GS} = 0 \text{ V}$		_	-1.2	V

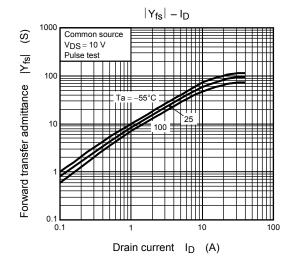
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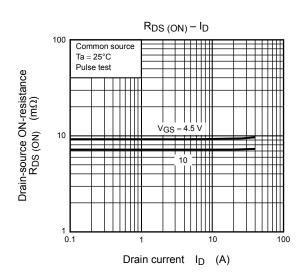


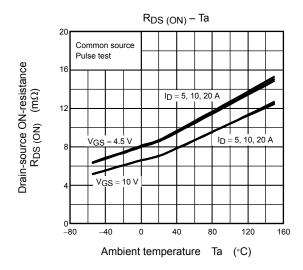


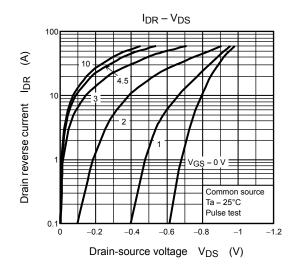


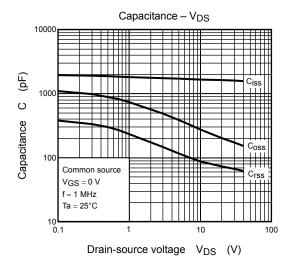


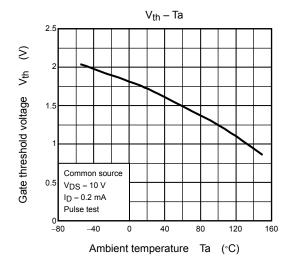


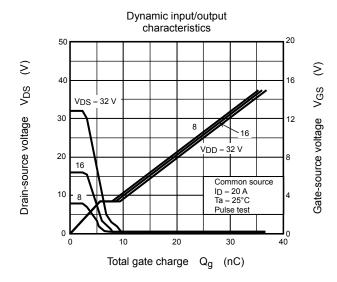




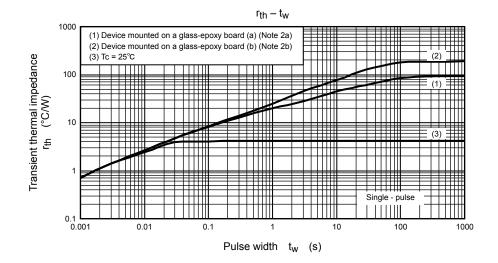


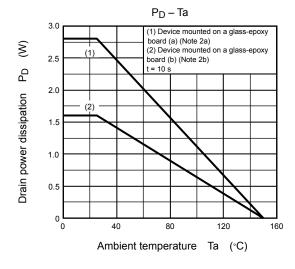


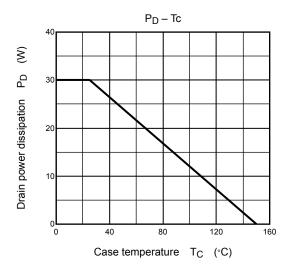


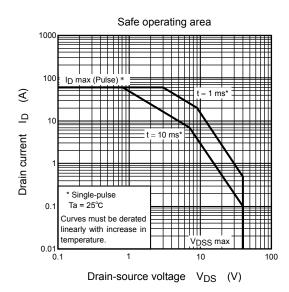


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